

# List of reference symbols

1	Si semiconductor substrate
OS	Top side
2, 2a	Pad oxide
3, 3a, 3b	Pad nitride
5	Trench
40	Conductive polyregion
10, 10a, 10b	Insulation collar
20, 20a, 20b	Conductive filling (e.g. polysilicon)
15a, 15b	Buried contact
16a, 16b	Insulation region
G1, G2	Trench
GK1, GK2	Trench capacitor
30, 30a, 30b	Capacitor dielectric
S1, S2, S3	Source region
D1, D2	Drain region
K2	Channel region
WL, WL1, WL2, WL3	Word line
GS1, GS2, GS3	Gate stack
GI1, GI2, GI3	Gate insulator
I	Insulation layer
F	Minimum length unit
BLK	Bit line contact
BL	Bit line
DT	Trench
AA	Active region
STI	Isolation region (shallow trench isolation)
UC	Area unit cell
KS, KS1, KS2	Contact region
IS, IS1, IS2	Insulation region
50	Silicon nitride liner
55	Liner made of amorphous undoped silicon
60	Shaded region of 55
55'	Implanted region of 55
55''	Oxidized implanted region of 55

I1-I7	Implantation
300	Polysilicon liner
300', 300''	Implanted region of 300
310	Shaded region of 300
310'	Oxidized liner
320, 740	Conductive filling
500	Oxynitride liner
700	Etching stop layer
710	Sacrificial polysilicon layer
720, 730	Insulation region
800	Hard mask layer
810	Mask
610	Silicon oxynitride